
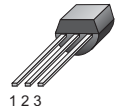


### HAOPIN MICROELECTRONICS CO.,LTD.

#### Description

Glass passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

Symbol		Simplified outline	
		 TO-92	
Pin	Description		
1	Cathode		
2	anode		
3	gate		
TAB	anode		

#### Applications:

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

#### Features

- ◆ Blocking voltage to 600 V
- ◆ On-state RMS current to 0.8 A
- ◆ Ultra low gate trigger current

SYMBOL	PARAMETER	Value	Unit
$V_{DRM}$	Repetitive peak off-state voltages PCR406 PCR606	400 600	V
$I_T (RMS)$	RMS on-state current (full sine wave)	0.8	A
$I_{TAV}$	Average On-state Current	0.5	A

SYMBOL	PARAMETER	CONDITIONS	Value	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance. junction to Case		75	-	-	°C/W
$R_{\theta JA}$	Thermal Resistance. Junction to Ambient		200	-	-	°C/W

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Limiting values in accordance with the Maximum system(IEC 134)

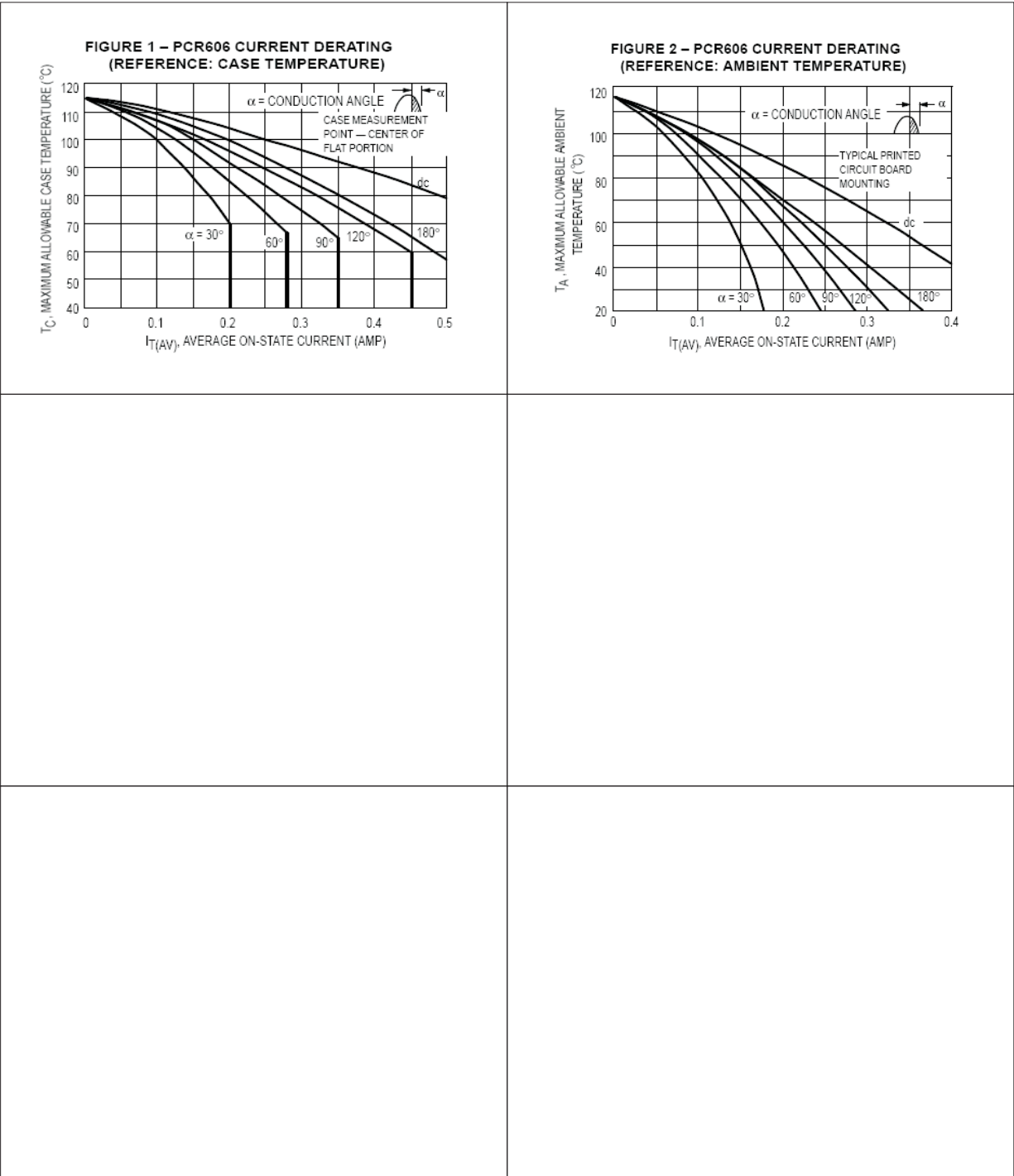
SYMBOL	PARAMETER	CONDITIONS	MIN	Value	UNIT
$V_{DRM}$ $V_{RRM}$	Peak Repetitive Forward and Reverse Blocking Voltage	$T_j=25$ to $125^{\circ}\text{C}$ , $R_{GK}=1\text{K}\Omega$ PCR406 PCR606	-	400 600	V
$I_{T(RMS)}$	Forwrd Current RMS seeFigures1&2	All Conduction Angles	-	0.8	A
$I_{GFM}$	Peak Gate Current-Forward	$T_a=25^{\circ}\text{C}$	-	1	A
$I^2t$	Circuit Fusing Considerations	$t=8.3\text{ms}$	-	0.415	$\text{A}^2\text{s}$
$I_{TSM}$	Peak Forward surge Current, $T_A=25^{\circ}\text{C}$	$1/2$ Cycle, Sing Wave, $60\text{Hz}$	- -	10 -	A A
$P_{GF(AV)}$	Average gate Power-Forward	$T_a=25^{\circ}\text{C}$	-	0.01	W
$T_j$	Operating junction temperature range@rated	$V_{RRM}$ and $V_{DRM}$	-40	125	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature Range		-40	125	$^{\circ}\text{C}$
$P_{GM}$	Peak gate power -Forward	$T_a=25^{\circ}\text{C}$	-	0.1	W

$T_j=25^{\circ}\text{C}$  unless otherwise stated

SYMBOL	TEST	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
$I_{GT}$	Gate trigger current Contionuous dc	$T_a=25^{\circ}\text{C}$ , Anode Voltage= $7\text{Vdc}$ , $R_L=100\text{Ohms}$	-	-	200	$\mu\text{A}$
$V_{GT}$	Gate trigger voltage Continuous dc	Anode voltage= $7\text{vdc}$ , $R_L=100\text{Ohms}$ Anode voltage=Rated $V_{DRM}$ , $R_L=100\text{Ohms}$	- - 0.1	- - -	0.8 1.2 -	V V V
$V_{TM}$	Forward On Voltage	$I_{TM}=1\text{A Peak}@T_A=25^{\circ}\text{C}$	-	-	1.7	V
$I_H$	Holding current	$T_C=25^{\circ}\text{C}$ / $T_C=-40^{\circ}\text{C}$	-	-	5/10	mA
$I_{DRM}$ $I_{RRM}$	Peak Forward or Reverse Blocking Current	$T_c=25^{\circ}\text{C}$ , $T_c=125^{\circ}\text{C}$ ,	- -	- -	10 100	$\mu\text{A}$
$I_{FGM}$	Peak gate forward current		-	-	-	A

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#### Description

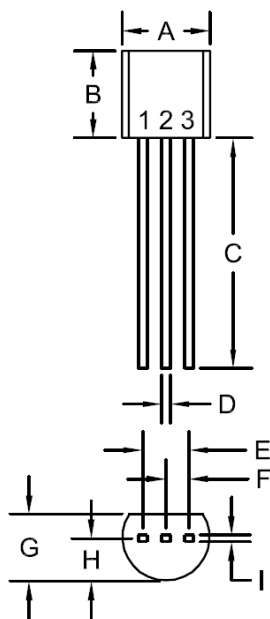


MECHANICAL DATA

Dimensions in mm

Net Mass:0.2 g

TO-92



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

R1